

# Sarvesh Dubey

## List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Investigating the Impact of Self-Heating Effects on some Thermal and Electrical Characteristics of Dielectric Pocket Gate-all-around (DPGAA) MOSFETs. Silicon, 2022, 14, 7053-7063.	3.3	7
2	Impact of Different Gate Dielectric Materials on Analog/RF Performance of Dielectric-Pocket Double Gate-All-Around (DPGAA) MOSFETs. Silicon, 2022, 14, 9361-9366.	3.3	1
3	An efficient analytical scheme with convergence analysis for computational study of local fractional Schrödinger equations. Mathematics and Computers in Simulation, 2022, 196, 296-318.	4.4	13
4	Design and investigation of $ZnO$ based thin film transistors for high-speed AMLCD pixel circuit applications. Superlattices and Microstructures, 2022, 164, 107122.	3.1	3
5	Impact of Temperature on Analog/RF Performance of Dielectric Pocket Gate-all-around (DPGAA) MOSFETs. Silicon, 2021, 13, 2071-2075.	3.3	12
6	Back Bias Induced Modeling of Subthreshold Characteristics of SOI Junctionless Field Effect Transistor (JLFET). Silicon, 2021, 13, 1961-1967.	3.3	1
7	An Ultra-Low-Power Black Phosphorus (B-Ph)/Si Heterojunction Dopingless-Tunnel FET (HD-TFET) with Enhanced Electrical Characteristics. Superlattices and Microstructures, 2021, 149, 106752.	3.1	8
8	Modeling the threshold voltage of core-and-outer gates of ultra-thin nanotube Junctionless-double gate-all-around (NJL-DGAA) MOSFETs. Microelectronics Journal, 2021, 113, 105104.	2.0	24
9	Effect of Substrate Induced Surface Potential (SISP) on Threshold Voltage of SOI Junction-Less Field Effect Transistor (JLFET). Silicon, 2020, 12, 921-926.	3.3	6
10	Investigating linearity and effect of temperature variation on analog/RF performance of dielectric pocket high-k double gate-all-around (DP-DGAA) MOSFETs. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	9
11	Semianalytical Threshold Voltage Model of a Double-Gate Nanoscale RingFET for Terahertz Applications in Radiation-Hardened (Rad-Hard) Environments. Journal of Electronic Materials, 2019, 48, 6366-6371.	2.2	3
12	Investigating the Possibility to Extend Planar Technology to 10 nm Scale with UTBB DMG SSOI MOSFETs. , 2019, , .		1
13	GaN nanophosphors for white-light applications. Optical Materials, 2018, 75, 61-67.	3.6	10
14	Fabrication of ZnO Thin Films by Sol-Gel Spin Coating and Their UV and White-Light Emission Properties. Journal of Electronic Materials, 2017, 46, 6029-6037.	2.2	15
15	Effects of Elevated Source/Drain and Side Spacer Dielectric on the Drivability Optimization of Non-abrupt Ultra Shallow Junction Gate Underlap DG MOSFETs. Journal of Electronic Materials, 2017, 46, 520-526.	2.2	3
16	Subthreshold Current and Swing Modeling of Gate Underlap DG MOSFETs with a Source/Drain Lateral Gaussian Doping Profile. Journal of Electronic Materials, 2017, 46, 579-584.	2.2	2
17	Analytical modeling of threshold voltage for symmetrical silicon nano-tube field-effect-transistors (Si-NT FETs). Journal of Computational Electronics, 2016, 15, 516-524.	2.5	25
18	Analytical Modeling of Potential Distribution and Threshold Voltage of Gate Underlap DG MOSFETs with a Source/Drain Lateral Gaussian Doping Profile. Journal of Electronic Materials, 2016, 45, 2184-2192.	2.2	8

#	ARTICLE	IF	CITATIONS
19	A threshold voltage model of short-channel fully-depleted recessed-source/drain (Re-S/D) SOI MOSFETs with high- $k$ dielectric. Chinese Physics B, 2015, 24, 108505.	1.4	2
20	Quasi-3D subthreshold current and subthreshold swing models of dual-metal quadruple-gate (DMQG) MOSFETs. Journal of Computational Electronics, 2015, 14, 582-592.	2.5	11
21	Analytical model for subthreshold current and subthreshold swing of short-channel double-material-gate MOSFETs with strained-silicon channel on silicon-germanium substrates. Journal of Semiconductors, 2014, 35, 104002.	3.7	11
22	Analytical modeling of subthreshold current and subthreshold swing of Gaussian-doped strained-Si-on-insulator MOSFETs. Journal of Semiconductors, 2014, 35, 084001.	3.7	16
23	Threshold Voltage Modeling of Short-Channel DG MOSFETs with Non-Uniform Doping in the Vertical Direction. Environmental Science and Engineering, 2014, , 263-266.	0.2	0
24	Analytical subthreshold current and subthreshold swing models of short-channel dual-metal-gate (DMG) fully-depleted recessed-source/drain (Re-S/D) SOI MOSFETs. Journal of Computational Electronics, 2014, 13, 467-476.	2.5	6
25	Analog and radio-frequency (RF) performance evaluation of fully-depleted (FD) recessed-source/drain (Re-S/D) SOI MOSFETs. Superlattices and Microstructures, 2014, 76, 77-89.	3.1	6
26	Analytical Modeling of Threshold Voltage of Short-Channel Strained-Si on Silicon-Germanium-On-Insulator (SGOI) Metal-Oxide-Semiconductor Field-Effect Transistors with Localized Charges. Journal of Computational and Theoretical Nanoscience, 2014, 11, 165-172.	0.4	1
27	Analytical Modeling of Threshold Voltage of Ion-Implanted Strained-Si-on-Insulator (SSOI) MOSFETs. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 442-448.	0.5	10
28	An Analytical Study of Ion Implanted Strained-Si on SOI MOSFETs for Optimizing Switching Characteristics. Environmental Science and Engineering, 2014, , 203-206.	0.2	0
29	Two-dimensional modeling of subthreshold current and subthreshold swing of double-material-gate (DMG) strained-Si (s-Si) on SGOI MOSFETs. Journal of Computational Electronics, 2013, 12, 275-280.	2.5	9
30	An analytical model of threshold voltage for short-channel double-material-gate (DMG) strained-Si (s-Si) on Silicon-Germanium-on-Insulator (SGOI) MOSFETs. Journal of Computational Electronics, 2013, 12, 20-28.	2.5	23
31	Analytical modeling and simulation of subthreshold characteristics of back-gated SSGOI and SSOI MOSFETs: A comparative study. Current Applied Physics, 2013, 13, 1778-1786.	2.4	10
32	An Analytical Threshold Voltage Model for Triple-Material Cylindrical Gate-All-Around (TM-CGAA) MOSFETs. IEEE Nanotechnology Magazine, 2013, 12, 766-774.	2.0	46
33	An analytical surface potential modeling of fully-depleted symmetrical double-gate (DG) strained-Si MOSFETs including the effect of interface charges. , 2013, , .		2
34	A rigorous simulation based study of gate misalignment effects in gate engineered double-gate (DG) MOSFETs. Superlattices and Microstructures, 2013, 60, 263-279.	3.1	22
35	Analytical models of subthreshold current and swing of short-channel strained-Si (s-Si) on Silicon-Germanium-on-Insulator (SGOI) MOSFETs. Superlattices and Microstructures, 2013, 58, 1-10.	3.1	12
36	An analytical threshold voltage model for a short-channel dual-metal-gate (DMG) recessed-source/drain (Re-S/D) SOI MOSFET. Superlattices and Microstructures, 2013, 60, 580-595.	3.1	22

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37	Back gated strained-Si (s-Si) on silicon-germanium-on-insulator (SGOI) MOSFETs for improved switching speed and short-channel effects (SCEs). , 2013, , .		0
38	On-current modeling of short-channel double-gate (DG) MOSFETs with a vertical Gaussian-like doping profile. Journal of Semiconductors, 2013, 34, 054001.	3.7	12
39	An Analytical Model for the Threshold Voltage of Short-Channel Double-Material-Gate (DMG) MOSFETs with a Strained-Silicon (s-Si) Channel on Silicon-Germanium (SiGe) Substrates. Journal of Semiconductor Technology and Science, 2013, 13, 367-380.	0.4	6
40	An analytical modeling of interface charge induced effects on subthreshold current and subthreshold swing of strained-Si (s-Si) on Silicon-Germanium-on-Insulator (SGOI) MOSFETs. , 2012, , .		0
41	A 2D analytical modeling approach for nanoscale strained-Si (s-Si) on silicon-germanium-on-insulator (SGOI) MOSFETs by evanescent mode analysis. , 2012, , .		0
42	Analytical modeling of subthreshold current and subthreshold swing of short-channel triple-material double-gate (TM-DG) MOSFETs. Superlattices and Microstructures, 2012, 51, 715-724.	3.1	24
43	A two-dimensional model for the subthreshold swing of short-channel double-gate metal-oxide-semiconductor field effect transistors with a vertical Gaussian-like doping profile. Journal of Applied Physics, 2011, 109, 054508.	2.5	17
44	Analytical modeling and ATLAS-based simulation of the surface potential of double-material-gate strained-Si on Silicon-Germanium-on-Insulator (DMGSGOI) MOSFETs. , 2011, , .		1
45	A two-dimensional analytical model for threshold voltage of short-channel triple-material double-gate metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2010, 108, 074508.	2.5	59
46	Subthreshold swing model for asymmetric 3T double gate (DG) MOSFETs. , 2010, , .		0
47	A two-dimensional model for the potential distribution and threshold voltage of short-channel double-gate metal-oxide-semiconductor field-effect transistors with a vertical Gaussian-like doping profile. Journal of Applied Physics, 2010, 108, .	2.5	60
48	A Two-Dimensional Model for the Surface Potential and Subthreshold Current of Doped Double-Gate (DG) MOSFETs with a Vertical Gaussian-Like Doping Profile. Journal of Nanoelectronics and Optoelectronics, 2010, 5, 332-339.	0.5	5
49	A comparative analysis of two computational schemes for solving local fractional Laplace equations. Mathematical Methods in the Applied Sciences, 0, , .	2.3	14
50	Exploring the Self-Heating Effects & Its Impact on Thermal Noise for Dielectric Pocket Packed Double-Gate-All-Around (DPP-DGAA) MOSFETs. Silicon, 0, , 1.	3.3	4
51	Electronic Noise Analysis of Source-Engineered Phosphorene/Si Heterojunction Dopingless Tunnel-FET. Silicon, 0, , .	3.3	0